

## **N-Channel Power MOSFET**

800V, 0.3A, 21.6Ω

SOT-223

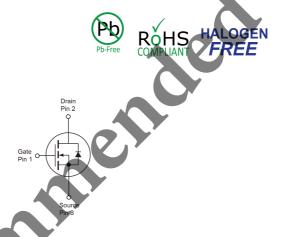
#### **FEATURES**

- Advanced planar process
- 100% avalanche tested
- Fast switching

#### APPLICATION

- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS			
PARAMETER	VALUE	UNIT	
V <sub>DS</sub>	800	V	
R <sub>DS(on)</sub> (max)	21.6	Ω	
Qg	5	nC	



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	800	V	
Gate-Source Voltage	V <sub>GS</sub>	±30	V	
Continuous Drain Current	I <sub>D</sub>	0.3	А	
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	1	А	
Single Pulse Avalanche Energy (Note 2)	E <sub>AS</sub>	90	mJ	
Avalanche Current, Repetitive or Not-Repetitive (Note 1)	I <sub>AR</sub>	1	А	
Total Power Dissipation @ $T_c = 25^{\circ}C$	P <sub>DTOT</sub>	2.1	W	
Operating Junction Temperature	TJ	150	°C	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Ambient Thermal Resistance	R <sub>eja</sub>	60	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air



Taiwan Semiconductor

ELECTRICAL SPECIFICA	<b>TIONS</b> ( $T_A = 25^{\circ}C$ unles	ss otherwise n	oted)			-
PARAMETER	CONDITIONS	SYMBOL	MIN	ΤΥΡ	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	$BV_{DSS}$	800			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.15A$	R <sub>DS(ON)</sub>		18	21.6	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	3		5	V
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I <sub>DSS</sub>			25	μA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>		-	±10	μA
Forward Transconductance	$V_{DS} = 40V, I_{D} = 0.1A$	<b>g</b> <sub>fs</sub>		0.36		S
Diode Forward Voltage	$I_{S} = 0.2A, V_{GS} = 0V$	V <sub>SD</sub>			1.4	V
Dynamic <sup>(Note 3)</sup>						
Total Gate Charge		Qg		5	6	
Gate-Source Charge	$V_{DS} = 640V, I_D = 0.3A,$ $V_{GS} = 10V$	Q <sub>gs</sub>		1		nC
Gate-Drain Charge		Q <sub>gd</sub>		2		
Input Capacitance		C <sub>iss</sub>		155	200	
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		20	26	pF
Reverse Transfer Capacitance		Crss		2.7	4	
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 0.3A,$ $V_{DS} = 400V, R_G = 25\Omega$	t <sub>d(on)</sub>		10	30	
Turn-On Rise Time		t <sub>r</sub>		20	50	
Turn-Off Delay Time		t <sub>d(off)</sub>		16	45	ns
Turn-Off Fall Time		t <sub>f</sub>		25	60	1

#### Note:

- 1. Pulse test: pulse width <= 300uS, duty cycle <= 2%
- 2.  $(V_{DD} = 50V, I_{AS} = 0.8A, L = 170mH, R_G = 25\Omega)$
- 3. For design reference only, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



#### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM1N80CW RPG	SOT-223	2,500pcs / 13" Reel

Note:

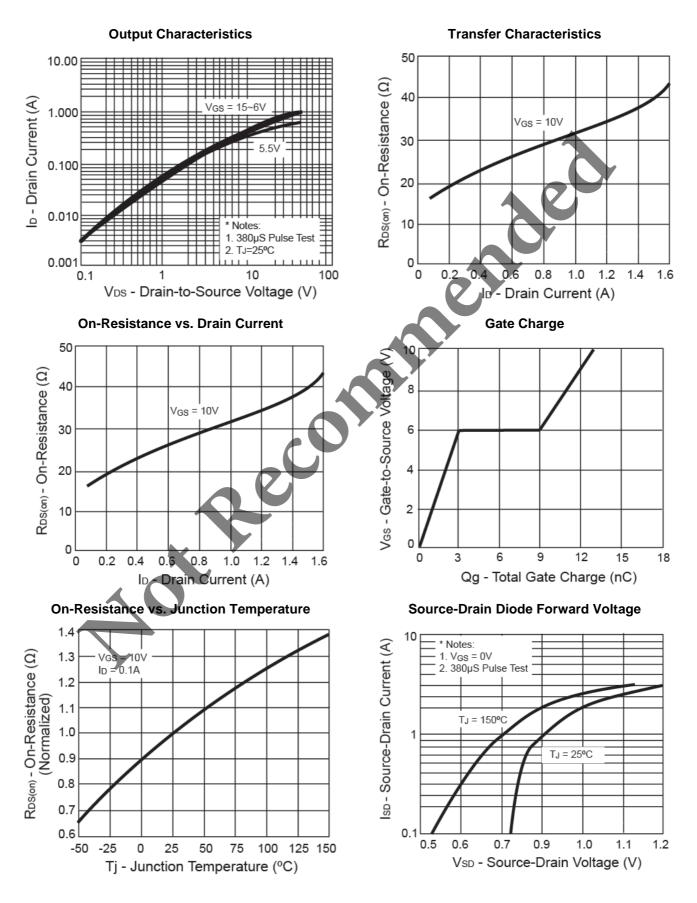
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

Halogen-free according to IEC 61249-2-21 definition Reconnection 2.



### **CHARACTERISTICS CURVES**

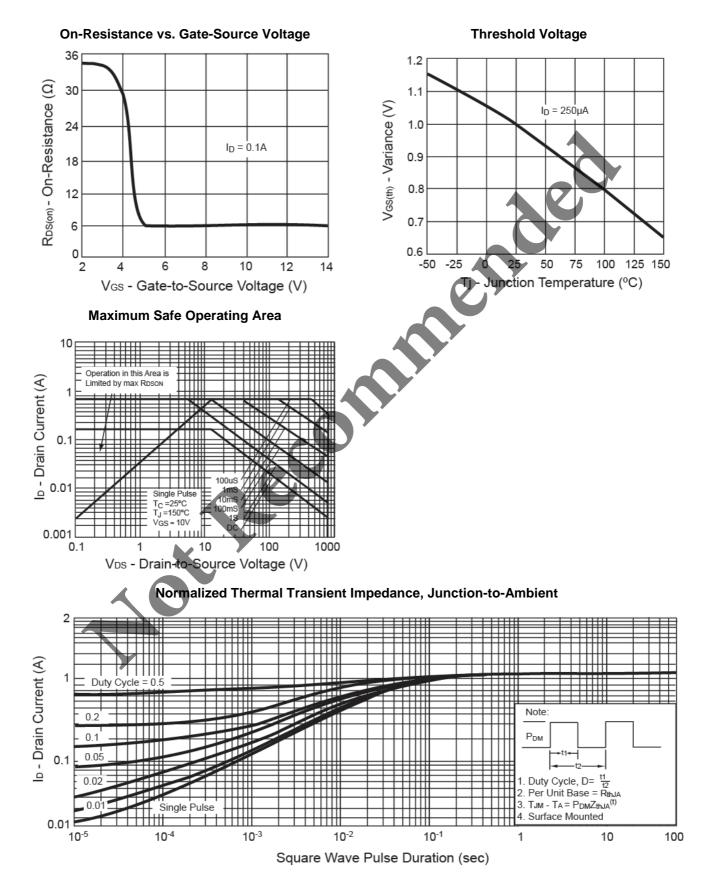
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 





#### **CHARACTERISTICS CURVES**

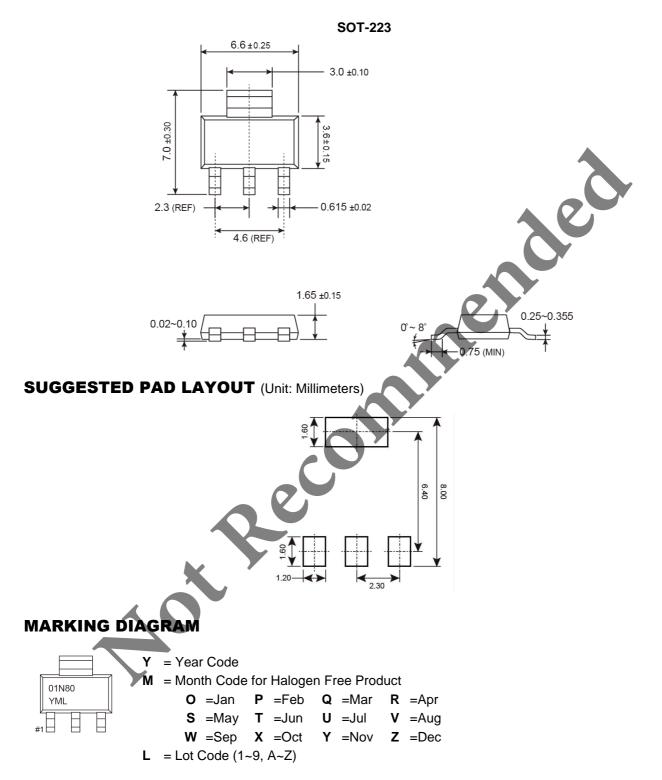
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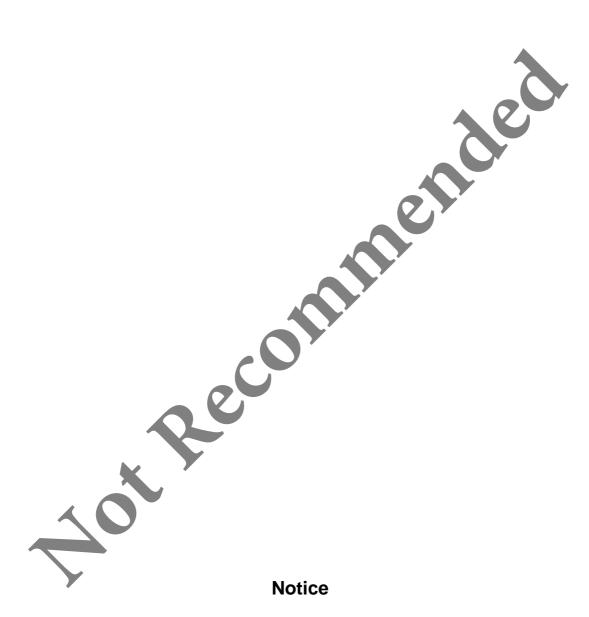




#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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